



P-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	-40 V
I_D	-30 A
$R_{DS(ON)}$ (at $V_{GS}=-10V$)	30 m
$R_{DS(ON)}$ (at $V_{GS}=-4.5V$)	45 m
100% EAS Tested	
100% V_{DS} Tested	

General Description

Trench Power LV MOSFET technology
Low $R_{DS(on)}$ & FOM
Extremely low switching loss
Excellent stability and uniformity
High density cell design for low $R_{DS(ON)}$
Moisture Sensitivity Level 1
Epoxy Meets UL 94 V-0 Flammability Rating
Halogen Free

Applications

Absolute Maximum Ratings (T_A)

YJD30P04A



Typical Electrical and Thermal Characteristics Diagrams

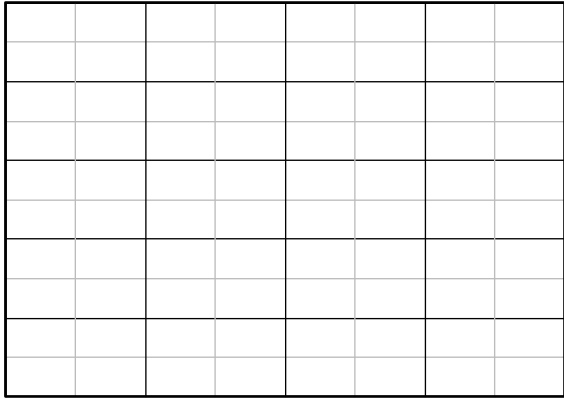


Figure 7. $R_{DS(on)}$ VS Drain Current

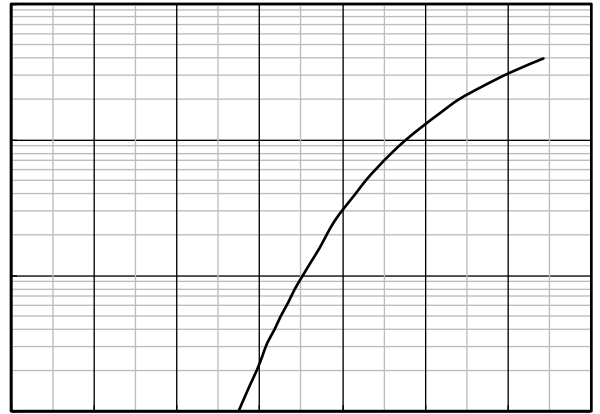


Figure 8. Forward characteristics of reverse diode

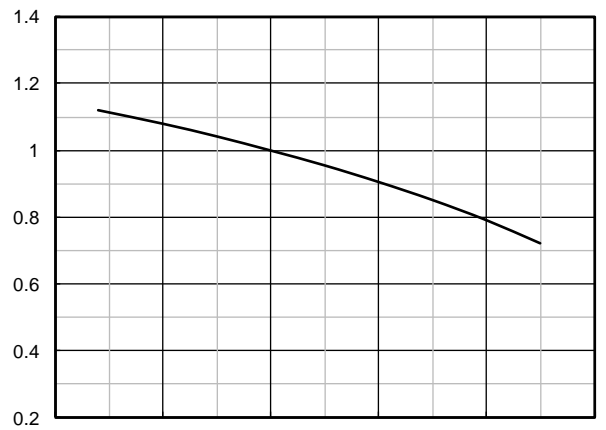


Figure 9. Normalized breakdown voltage

Figure 10. Normalized Threshold voltage

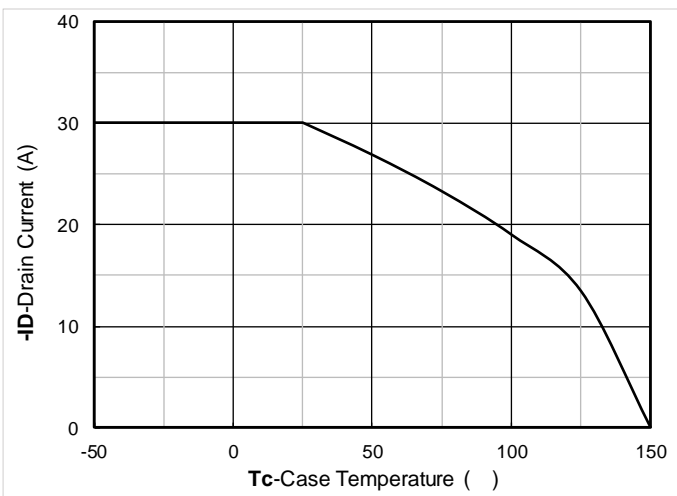


Figure 11. Current dissipation

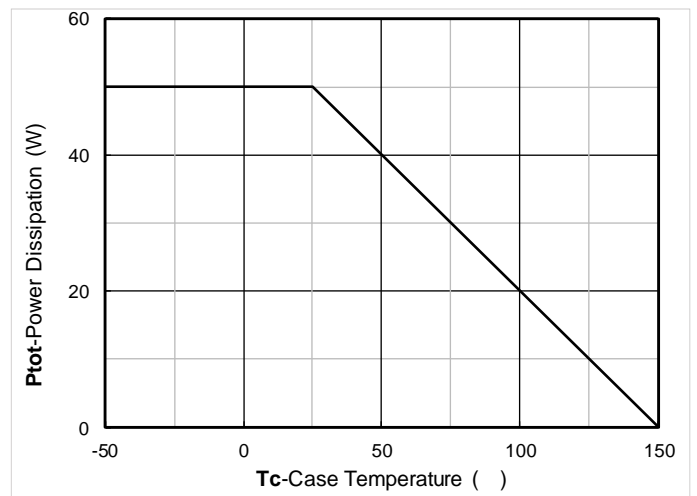
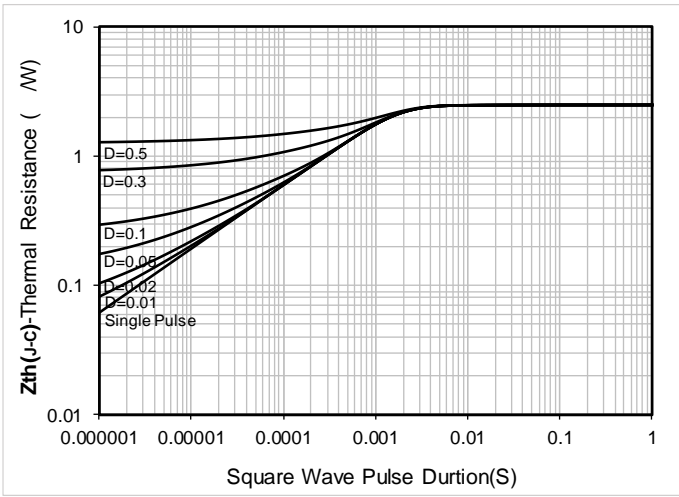


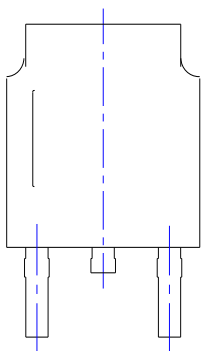
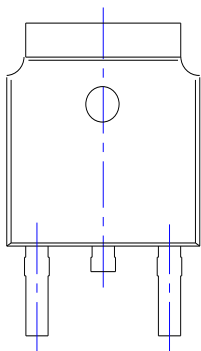
Figure 12. Power dissipation





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TO-252-B Package information



SYMBOL	DIMENSIONS				
	INCHES				
	MIN.	NOM.			
A1	0.000				
A2	0.087	0.091			
A3	0.035	0.039			
b	0.026	0.030			
c	0.018	0.020			
D	0.256	0.260			
D1					
D2	0.181	0.189			
E	0.390	0.398			
E1	0.236	0.240			

NOTE:
1.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
3.THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.



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